

RF ESD Protection Diodes

- ESD / transient protection of RF antenna / interfaces or ultra high speed data lines acc. to: IEC61000-4-2 (ESD): ± 20 kV (contact) IEC61000-4-4 (EFT): 40 A (5/50 ns) IEC61000-4-5 (surge): 10 A (8/20 μs)
- Ultra low capacitance of 1 pF typ. (0.5 pF per diode)
- Low clamping voltage
- Pb-free (ROHS compliant) package

Applications in anti-parallel configuration

• For low RF signal levels without superimposed DC voltage: e.g. GPS, WLAN, Bluetooth

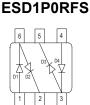
Applications in rail-to-rail configuration

 For high RF signal levels or low RF signal levels with superimposed DC voltage: e.g. HDMI, S-ATA, Gbit Ethernet

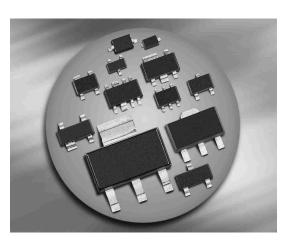


ESD1P0RFW





Туре	Package	Configuration	Marking	
ESD1P0RFS	SOT363	2 channels	E6s	
ESD1P0RFW	SOT323	1 channel	E6s	



1



Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit		
ESD contact discharge ¹⁾	V _{ESD}	20	kV		
Peak pulse current ($t_p = 8 / 20 \ \mu s$) ²⁾	I _{pp}	10	A		
Operating temperature range	T _{op}	-55150	°C		
Storage temperature	T _{stg}	-65150			

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics -					
Reverse working voltage ³⁾	V _{RWM}	-	-	70	V
Reverse current	I _R	-	-	100	nA
V _R = 70 V					
Forward clamping voltage ²⁾	V _{FC}				V
/ _{PP} = 3 A, <i>t</i> _p = 8/20 μs		-	4	7	
<i>I</i> _{PP} = 10 A, <i>t</i> _p = 8/20 μs		-	12	15	
Line capacitance ⁴⁾	CT				pF
$V_{R} = 0 \text{ V}, f = 1 \text{ MHz}$		-	1	1.5	
$V_{\rm R}$ = 0 V, <i>f</i> = 1 MHz, for Application example 4		-	0.5	0.75	
Series inductance (per diode)	LS				nH
SOT323		-	1.4	-	
SOT363		-	1.6	-	

 $^{1}V_{\mbox{ESD}}$ according to IEC61000-4-2, only valid in anti-parallel or rail-to-rail connection.

Please refer to the application examples.

 $^{2}I_{pp}$ according to IEC61000-4-5, only valid in anti-parallel or rail-to-rail connection.

Please refer to the application examples.

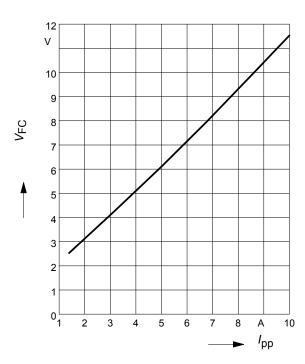
³Only valid in rail-to-rail configuration $V_{CC} \ge V_{RWM}$

⁴Total capacitance line to ground (2 diodes in parallel)



Forward clamping voltage $V_{\text{FC}} = f(I_{\text{PP}})$

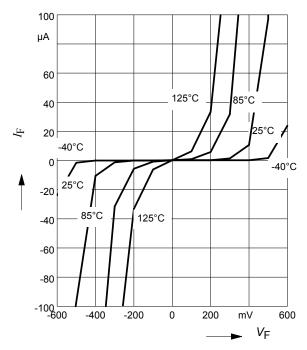
t_p = 8 / 20 μs



Forward current $I_F = f(V_F)$

T_A = Parameter

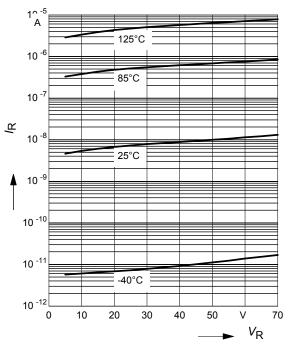
in anti-parallel configuration



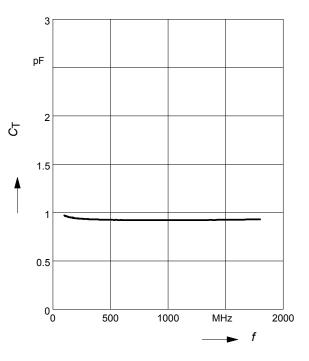
Reverse current $I_{R} = f(V_{R})$

 T_A = Parameter

in rail-to-rail configuration



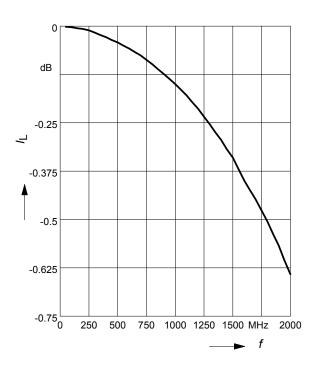
Line capacitance $C_T = f(f)$ $V_R = 0 V$







Insertion loss $|S_{21}|^2 = f(f)$ $V_R = 0 \text{ V}$, line to ground, Z = 50 Ω

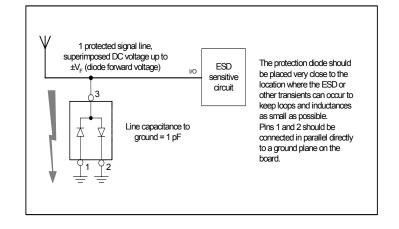






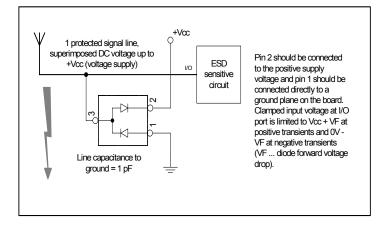
1. Application example ESD1P0RFW

1 channel, anti-parallel configuration



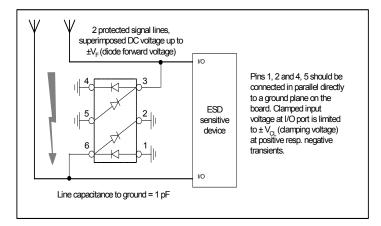
2. Application example ESD1P0RFW

1 channel, rail-to-rail configuration



3. Application example ESD1P0RFS

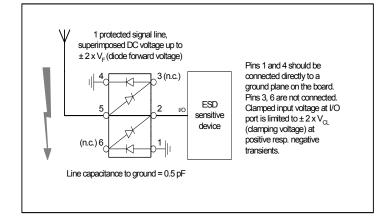
2 channels, anti-parallel configuration



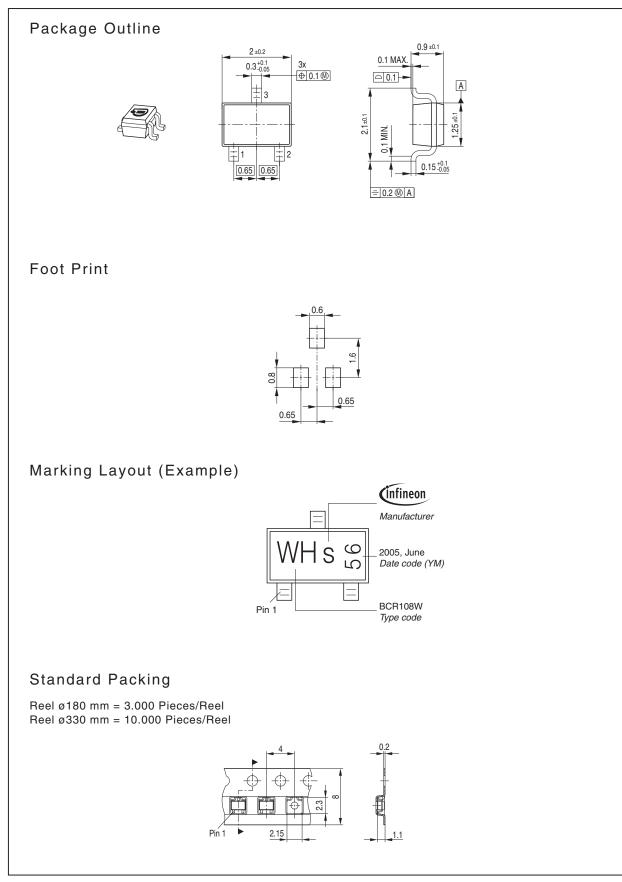


4. Application example ESD1P0RFS

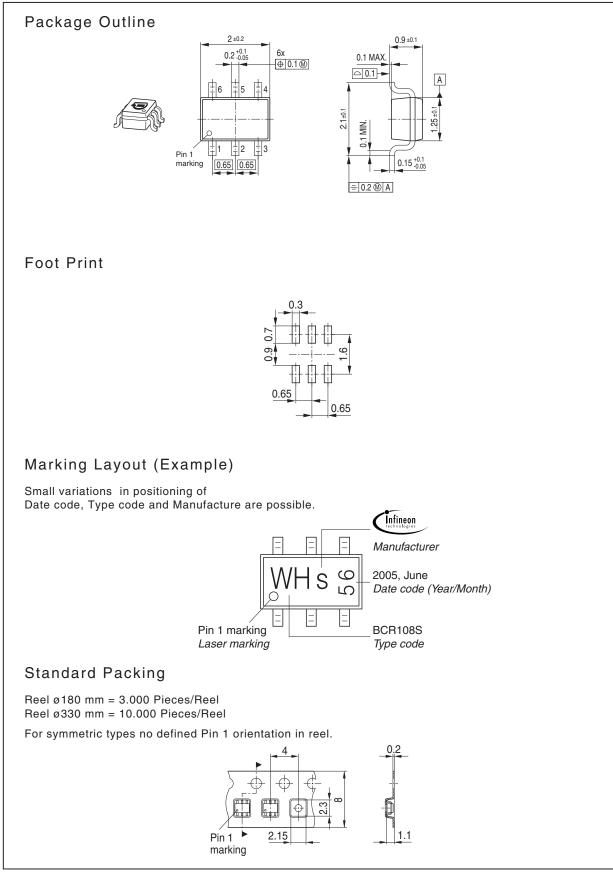
1 channel, low capacitance anti-parallel configuration















Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

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